

60V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = 25°C		
60V	66mΩ @ V _{GS} = 10V	5.0A		
	97mΩ @ V _{GS} = 4.5V	4.1A		

Description and Applications

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor control
- Backlighting
- DC-DC Converters
- Power management functions

Features and Benefits

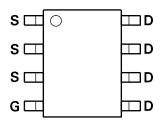
- Low on-resistance
- Fast switching speed
- "Green" component and RoHS compliant (Note 1)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

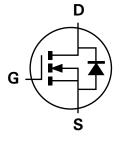
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See diagram below
- Terminals: Finish Matte Tin annealed over Copper lead frame.
 Solderable per MIL-STD-202, Method 208
- Weight: 0.074 grams (approximate)



Top View



Top View



Equivalent Circuit

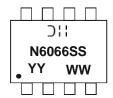
Ordering Information (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMN6066SSS-13	N6066SS	13	12	2,500

1. Diodes, Inc. defines "Green" products as those which are RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.'s "Green" Policy can be found on our website. For packaging details, go to our website.

Marking Information

Notes:



OH = Manufacturer's Marking
N6066SS = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 09 = 2009)
WW = Week (01 - 53)





Maximum Ratings @T_A = 25°C unless otherwise specified

	Characteristic		Symbol	Value	Unit
Drain-Source voltage			V_{DSS}	60	V
Gate-Source voltage (Note 2)			V _{GS}	±20	V
Single Pulsed Avalanche Er	nergy	(Note 7) E _{AS} 37.5		mJ	
Single Pulsed Avalanche Current		(Note 7)	I _{AS}	5.0	A
Continuous Drain current		(Note 4)		5.0	
	$V_{GS} = 10V$	$T_A = 70^{\circ}C$ (Note 4)	I _D	4.0	Α
		(Note 3)		3.7	
Pulsed Drain current	V _{GS} = 10V	(Note 5)	I _{DM}	23	Α
Continuous Source current (ntinuous Source current (Body diode) (Note		I _S	4.0	Α
Pulsed Source current (Body diode)		(Note 5)	I _{SM}	23	Α

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit		
Power dissipation	(Note 3)	9	1.56 12.5	W	
Linear derating factor	(Note 4)	P _D	2.81 22.5	mW/°C	
Thermal Decistores, Junction to Ambient	(Note 3)		80.0		
Thermal Resistance, Junction to Ambient	(Note 4)	$R_{ heta JA}$	44.5	°C/W	
Thermal Resistance, Junction to Lead	(Note 6)	$R_{ heta JL}$	37.0		
Operating and storage temperature range		T _J , T _{STG}	-55 to 150	°C	

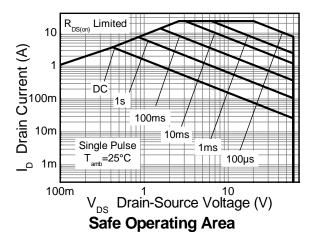
Notes:

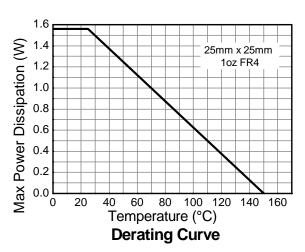
- 2. AEC-Q101 V_{GS} maximum is $\pm 16 \text{V}.$
- 3. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 4. Same as note (3), except the device is measured at $t \le 10$ sec.
- 5. Same as note (3), except the device is pulsed with D= 0.02 and pulse width 300 µs. The pulse current is limited by the maximum junction temperature.
- 6. Thermal resistance from junction to solder-point (at the end of the drain lead). 7. UIS in production with L = 3.0mH, I_{AS} = 5.0A, R_{G} = 25 Ω , V_{DD} =50V, starting T_{J} = 25°C.

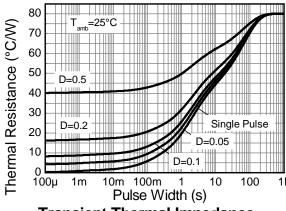


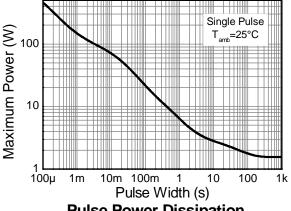


Thermal Characteristics









Transient Thermal Impedance

Pulse Power Dissipation





Electrical Characteristics @T_A = 25°C unless otherwise specified

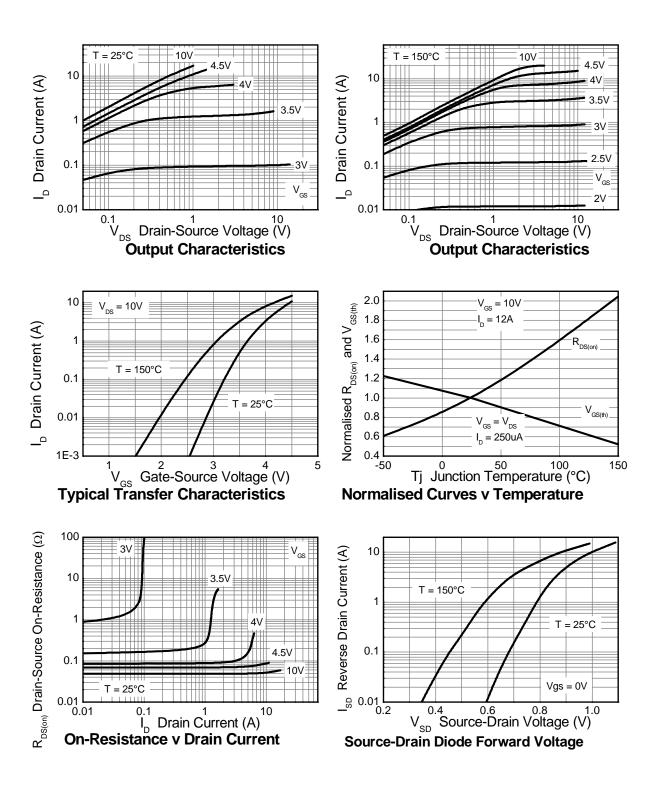
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$I_D = 250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	0.5	μА	V _{DS} = 60V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(th)}	1.0	_	3.0	V	$I_D = 250 \mu A, V_{DS} = V_{GS}$	
Static Drain-Source On-Resistance (Note 8)	_		0.048	0.066	Ω	$V_{GS} = 10V, I_D = 4.5A$	
Static Dialit-Source Off-Resistance (Note 6)	R _{DS} (ON)	_	0.068	0.097	22	$V_{GS} = 4.5V, I_D = 3.5A$	
Forward Transconductance (Notes 8 & 9)	g _{fs}	_	19.2	_	S	$V_{DS} = 15V, I_{D} = 6A$	
Diode Forward Voltage (Note 8)	V_{SD}	_	0.89	1.15	V	I _S = 4.5A, V _{GS} = 0V	
Reverse recovery time (Note 9)	t _{rr}		23	_	ns	1 2 4 A di/dt 100 A/v.o	
Reverse recovery charge (Note 9)	Qrr	_	19.7	_	nC	$I_S = 2.4A$, di/dt = 100A/ μ s	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	_	502	_	pF	V _{DS} = 30V, V _{GS} = 0V f = 1MHz	
Output Capacitance	Coss	_	45.7	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	27.1	_	pF	1 - 1101112	
Total Gate Charge (Note 10)	Qg	_	5.4	_	nC	V _{GS} = 4.5V	
Total Gate Charge (Note 10)	Qg	_	10.3	_	nC	V _{DS} = 30V	
Gate-Source Charge (Note 10)	Q _{gs}	_	1.7	_	nC	$V_{GS} = 10V$ $I_{D} = 4.5A$	
Gate-Drain Charge (Note 10)	Q _{gd}	_	3.2	_	nC		
Turn-On Delay Time (Note 10)	t _{D(on)}	_	2.7	_	ns		
Turn-On Rise Time (Note 10)	t _r	—	2.4		ns	$V_{DD} = 30V, V_{GS} = 10V$	
Turn-Off Delay Time (Note 10)	t _{D(off)}	—	14.7		ns	$I_D = 1A, R_G \cong 6.0\Omega$	
Turn-Off Fall Time (Note 10)	t _f	_	5.4	_	ns		

Notes:

- 8. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$; duty cycle $\leq 2\%$
- For design aid only, not subject to production testing.
 Switching characteristics are independent of operating junction temperatures.

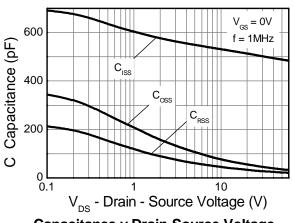


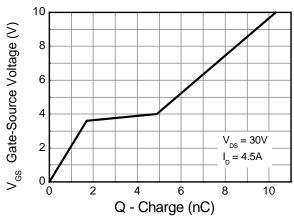
Typical Characteristics





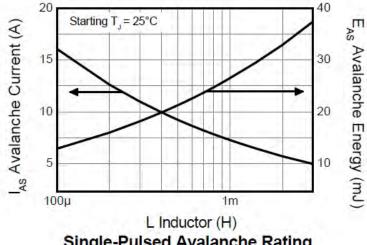
Typical Characteristics - continued





Capacitance v Drain-Source Voltage

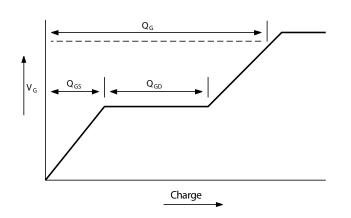
Gate-Source Voltage v Gate Charge

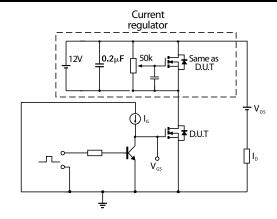


Single-Pulsed Avalanche Rating



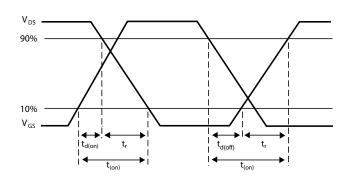
Test Circuits

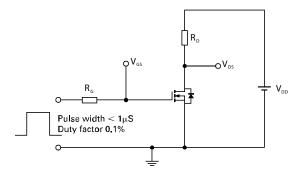




Basic gate charge waveform

Gate charge test circuit



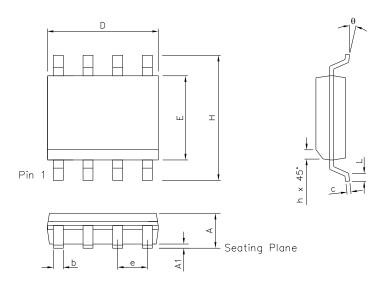


Switching time waveforms

Switching time test circuit

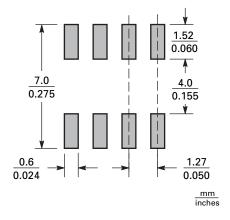


Package Outline Dimensions



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
Α	0.053	0.069	1.35	1.75	е	0.050 BSC		1.27 BSC	
A1	0.004	0.010	0.10	0.25	b	0.013	0.020	0.33	0.51
D	0.189	0.197	4.80	5.00	С	0.008	0.010	0.19	0.25
Н	0.228	0.244	5.80	6.20	θ	0°	8°	0°	8°
Е	0.150	0.157	3.80	4.00	h	0.010	0.020	0.25	0.50
L	0.016	0.050	0.40	1.27	-	-	-	-	-

Suggested Pad Layout







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